2SK2114, 2SK2115

Silicon N-Channel MOS FET

HITACHI

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Application

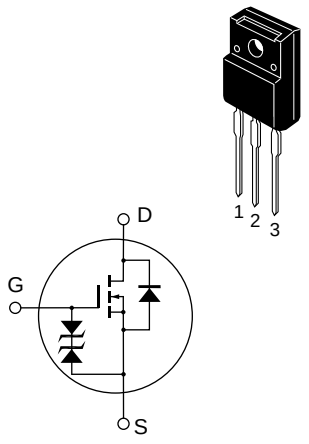
High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for Switching regulator

Outline

TO-220CFM



1. Gate
2. Drain
3. Source

Ordering Information

Type No.	V_{DSS}
2SK2114	450 V
2SK2115	500 V

Absolute Maximum Ratings (Ta = 25°C)

Item		Symbol	Ratings	Unit
Drain to source voltage	2SK2114	V_{DSS}	450	V
	2SK2115	V_{DSS}	500	
Gate to source voltage		V_{GSS}	±30	V
Drain current		I_D	5	A
Drain peak current		$I_{D(pulse)}$*[1]	20	A
Body to drain diode reverse drain current		I_{DR}	5	A
Channel dissipation		Pch*[2]	35	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	–55 to +150	°C

Notes 1. PW ≤ 10 µs, duty cycle ≤ 1 %
2. Value at Tc = 25 °C

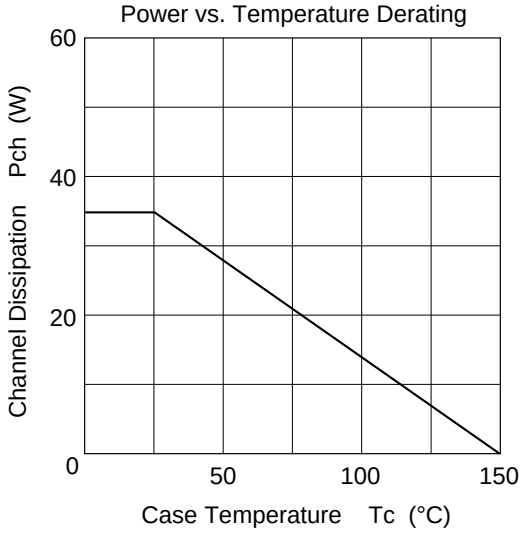
Electrical Characteristics (Ta = 25°C)

Item		Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	2SK2114	$V_{(BR)DSS}$	450	—	—	V	I_D = 10 mA, V_{GS} = 0
	2SK2115		500				
Gate to source breakdown voltage		$V_{(BR)GSS}$	±30	—	—	V	I_G = ±100 µA, V_{DS} = 0
Gate to source leak current		I_{GSS}	—	—	±10	µA	V_{GS} = ±25 V, V_{DS} = 0
Zero gate voltage drain current	2SK2114	I_{DSS}	—	—	250	µA	V_{DS} = 360 V, V_{GS} = 0
	2SK2115						V_{DS} = 400 V, V_{GS} = 0
Gate to source cutoff voltage		$V_{GS(off)}$	2.0	—	3.0	V	I_D = 1 mA, V_{DS} = 10 V
Static drain to source on state resistance	2SK2114	$R_{DS(on)}$	—	1.0	1.4	Ω	I_D = 2.5 A, V_{GS} = 10 V*[1]
	2SK2115		—	1.2	1.5		
Forward transfer admittance		$\|y_{fs}\|$	2.5	4.0	—	S	I_D = 2.5 A V_{DS} = 10 V*[1]
Input capacitance		Ciss	—	640	—	pF	V_{DS} = 10 V V_{GS} = 0 f = 1 MHz
Output capacitance		Coss	—	160	—	pF	
Reverse transfer capacitance		Crss	—	20	—	pF	
Turn-on delay time		$t_{d(on)}$	—	10	—	ns	I_D = 2.5 A V_{GS} = 10 V R_L = 12 Ω
Rise time		t_r	—	25	—	ns	
Turn-off delay time		$t_{d(off)}$	—	50	—	ns	
Fall time		t_f	—	30	—	ns	
Body to drain diode forward voltage		V_{DF}	—	0.95	—	V	I_F = 5 A, V_{GS} = 0
Body to drain diode reverse recovery time		t_{rr}	—	300	—	ns	I_F = 5 A, V_{GS} = 0, diF / dt = 100 A / µs

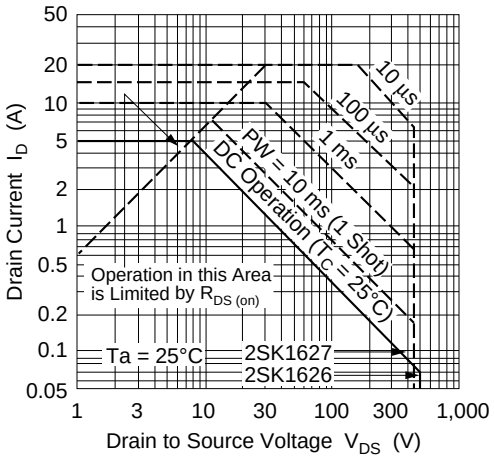
Note 1. Pulse Test

See characteristics curve of 2SK1155, 2SK1156.

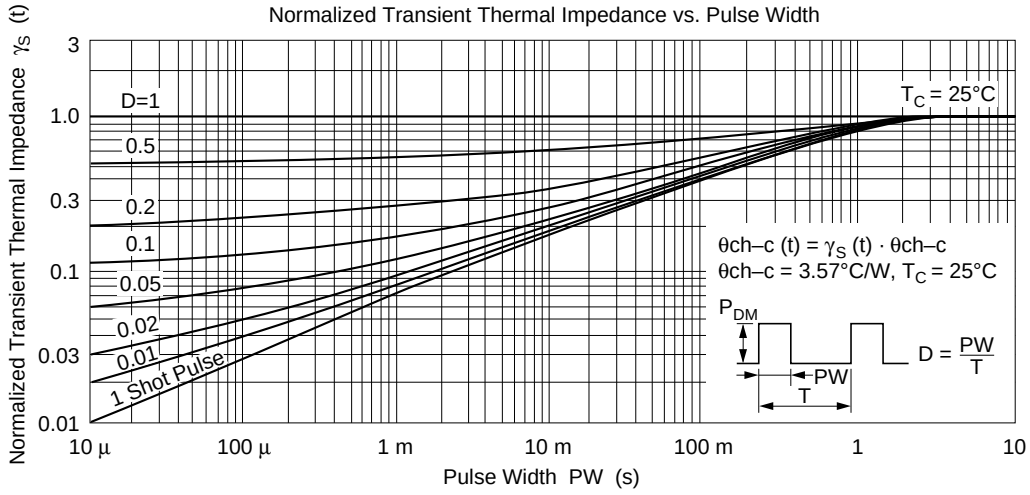
Power vs. Temperature Derating



Maximum Safe Operation Area



Normalized Transient Thermal Impedance vs. Pulse Width



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